Amendments to the Claims:

1. (original) A composition for forming porous film, the composition comprising siloxane polymer and one or more quaternary ammonium salts represented by following formula (1) or (2) :

$$[(R^1)_4N]^+[R^2X]^- \quad (1)$$

$$H_k[(R^1)_4N]_m^+ Y^{n-} \quad (2)$$

wherein R^1 independently represents a straight chain or branched alkyl or aryl group having 1 to 10 carbons which may have a substituent and R^1s may be same or different; R^2 represents a hydrogen atom or an straight chain or branched alkyl or aryl group having 1 to 10 carbons which may have a substituent; X represents CO_2, OSO_3 or SO_3; Y represents SO_4, SO_3, CO_3, O_2C-CO_2, NO_3 or NO_2; and k is 0 or 1, m is 1 or 2 and n is 1 or 2 in proviso that n=1 requires k=0 and m=1, and n=2 requires k=0 and m=2, or k=l and m=1.

2. (original) The composition for forming porous film according to Claim 1 wherein said siloxane polymer has a weight-average molecular weight of 10,000 to 1,000,000 using polyethylene as a standard.

3. (currently amended) A method for forming porous film comprising steps of applying said composition of Claim 1 [[or 2]] on a substrate to form a film and heating the film.

4. (currently amended) A porous film obtainable from said composition of Claim 1 [[or 2]].

5. (currently amended) An interlevel insulator film formable by said composition of Claim 1 [[or 2]].

6. (original) A semiconductor device comprising internal porous film which is formable by

applying on a substrate a composition for forming porous film comprising siloxane polymer and one or more quaternary ammonium salts represented by following formula (1) or (2):

$$[(R^1)_4N]^+[R^2X]^- \quad (1)$$

$$H_k [(R^1)_4N]_m^+ Y^{n-} \qquad (2)$$

wherein R^1 independently represents a straight chain or branched alkyl or aryl group having 1 to 10 carbons which may have a substituent and R^1s may be same or different; R^2 represents a hydrogen atom or an straight chain or branched alkyl or aryl group having 1 to 10 carbons which may have a substituent; X represents CO_2, OSO_3 or SO_3; Y represents SO_4, SO_3, CO_3, O_2C-CO_2, NO_3 or NO_2; and k is 0 or 1, m is 1 or 2 and n is 1 or 2 in proviso that n=1 requires k=0 and m=l, and n=2 requires k=0 and m=2, or k=1 and m=1;

and heating.

7. (original) The semiconductor device according to Claim 6 wherein said siloxane polymer has a weight-average molecular weight between 10,000 and 1,000,000 using polyethylene as a standard.

8. (currently amended) The semiconductor device according to Claim[[s]] 6[[or 7]] wherein said porous film is between metal interconnections in a same layer of multi-level interconnects, or is between upper and lower metal interconnection layers.